L Number	Hits	Search Text	DB	Time stamp
-	35	((((((257/295,298,310,532).CCLS.) and buried near3 contact) and	USPAT;	2003/07/17 17:41
		ferroelectric) and contact adj hole) and ((silicon adj oxynitride) or	US-PGPUB;	
		(silicon adj nitride))	ЕРО; ЛРО;	
		<u> </u>	DERWENT;	
			IBM TDB	
_	6203	(438/3,253,254,238,396).CCLS.	USPAT;	2003/07/17 17:47
	0200	(10010,200,200,200,000,000,000,000,000,00	US-PGPUB;	2005/07/17 17:17
			ЕРО; ЛРО;	
		*	DERWENT;	
			IBM_TDB	
	64	((438/3,253,254,238,396).CCLS.) and buried near3 contact and	USPAT;	2003/07/17 17:48
-	04	ferroelectric and contact adj hole	US-PGPUB;	2003/07/17 17:46
		lerroelectric and contact adj noie		
			ЕРО; ЛРО;	
			DERWENT;	
	,	((0.55/0.05.0.00.0.10.500.) CGV (1) 1 (1) 1 (1) 1 (1)	IBM_TDB	00001101001655
-	1	((257/295,298,310,532).CCLS.) and (insulat\$3 and substrate and	USPAT;	2003/12/02 16:55
		contact adj hole and (burry or burried))	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	0	((438/3,253,254,238,396).CCLS.) and (insulat\$3 and substrate and	USPAT;	2003/12/02 16:56
		contact adj hole and (burry or burried))	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	5458	(257/295,296,298,310,532).CCLS.	USPAT;	2003/12/02 16:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5458	(257/295,296,298,310,532).CCLS.	USPAT;	2003/12/02 16:56
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
-	6492	(438/3,253,254,238,396).CCLS.	IBM_TDB	
			USPAT;	2003/12/02 16:56
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	1586	(ferroelectric adj memory) and (insulat\$3 and substrate)	USPĀT;	2003/12/02 16:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	46	insulat\$3 and substrate and contact adj hole and (burry or burried)	USPAT;	2003/12/02 16:57
			US-PGPUB;	
			ЕРО; ЈРО;	
	-		DERWENT;	
	170		IBM_TDB	
<u> </u>	66	(((((((blocking adj layer) (etch adj stop)) with ((silicon adj nitride)	USPAT;	2003/12/03 07:51
	00	(((((Glocking adj layer) (etch adj sep)) with ((sincon adj minde)) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and	US-PGPUB;	
		dram) and capacitor) and ferroelectric	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
	c	((((((hlooking adi layor) (atah adi atan)) with ((ailiaan adi nitri da)	USPAT;	2003/12/02 07/52
-	5	((((((blocking adj layer) (etch adj stop)) with ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and		2003/12/03 07:52
			US-PGPUB;	
		dram) and capacitor) and ferroelectric and electrode with metallic	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	